

C3D06065I

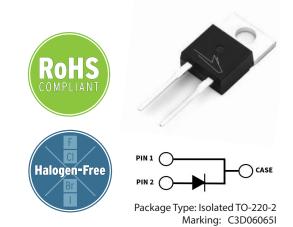
3rd Generation 650 V, 6 A Silicon Carbide Schottky Diode

Description

With the performance advantages of a Silicon Carbide (SiC) Schottky Barrier diode, power electronics systems can expect to meet higher efficiency standards than Si-based solutions, while also reaching higher frequencies and power densities. SiC diodes can be easily paralleled to meet various application demands, without concern of thermal runaway. In combination with the reduced cooling requirements and improved thermal performance of SiC products, SiC diodes are able to provide lower overall system costs in a variety of diverse applications.

Features

- Low Forward Voltage (V_F) Drop with Positive Temperature Coefficient
- Zero Reverse Recovery Current / Forward Recovery Voltage
- Temperature-Independent Switching Behavior
- Electrically Isolated Package (2.5kV)



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Applications

- Industrial Switched Mode Power Supplies
- Uninterruptible & AUX Power Supplies
- Boost for PFC & DC-DC Stages
- Solar Inverters
- AC/DC Converters

Maximum Ratings ($T_c = 25^{\circ}C$ Unless Otherwise Specified)

Parameter	Symbol	Value	Unit	Test Conditions	Notes	
Repetitive Peak Reverse Voltage	V _{RRM}	650				
DC Blocking Voltage	V _{DC}	650	V			
Continuous Forward Current		13	A	T _c = 25 °C	Fig. 3	
	I _F	6		T _c = 135 °C		
Repetitive Peak Forward Surge Current	I _{FRM}	24		$T_c = 25 \text{ °C}, t_p = 10 \text{ ms}, \text{ Half Sine Wave}$		
		16		$T_c = 110 \text{ °C}, t_p = 10 \text{ ms}, \text{ Half Sine Wave}$		
Non-Repetitive Forward Surge Current	I _{FSM}	63		$T_c = 25 \text{ °C}, t_p = 10 \text{ ms}, \text{ Half Sine Wave}$	Fig. 8	
		49		$T_c = 110 \text{ °C,} t_p = 10 \text{ ms}$, Half Sine Wave		
Non-Repetitive Peak Forward		540		$T_{c} = 25 \text{ °C}, t_{p} = 10 \mu \text{s}, \text{Pulse}$		
Surge Current	Г _{,Мах}	460		$T_{c} = 110^{\circ}C, t_{p} = 10 \ \mu s, Pulse$		
Power Dissipation	P _{tot}	45.5	W	$T_c = 25 \text{ °C}$	Fig. 4	
		19.5		T _c =110 °C		



Electrical Characteristics

Parameter	Symbol	Тур.	Max.	Unit	Test Conditions	Notes
		1.5	1.7	V	I _F = 6 A, T _j = 25 °C	Fig. 1
Forward Voltage	V _F	2.0	2.4		I _F = 6 A, T _j = 175 °C	
Reverse Current		8	40	μA	$V_{R} = 650 \text{ V}, \text{T}_{j} = 25 \text{ °C}$	Fig. 2
	I _R	15.5	160		V _R = 650 V, T _j = 175 °C	
Total Capacitive Charge	Q _c	15		nC	$V_{R} = 400 \text{ V}, \text{T}_{j} = 25 \text{ °C}, \text{I}_{F} = 6 \text{ A}$	Fig. 5
Total Capacitance	с	295		pF	$V_{R} = 0 V, T_{j} = 25 \text{ °C}, f = 1 \text{ MHz}$	
		28.5			$V_{R} = 200 V, T_{j} = 25 \text{ °C}, f = 1 \text{ MHz}$	
		25.5			$V_{R} = 400 \text{ V}, \text{T}_{j} = 25 \text{ °C}, \text{f} = 1 \text{ MHz}$	
Capacitance Stored Energy	E _c	2.3		μJ	$V_{R} = 400 V$	Fig. 7

Notes:

SiC Schottky Diodes are majority carrier devices, so there is no reverse recovery charge.

Thermal & Mechanical Characteristics

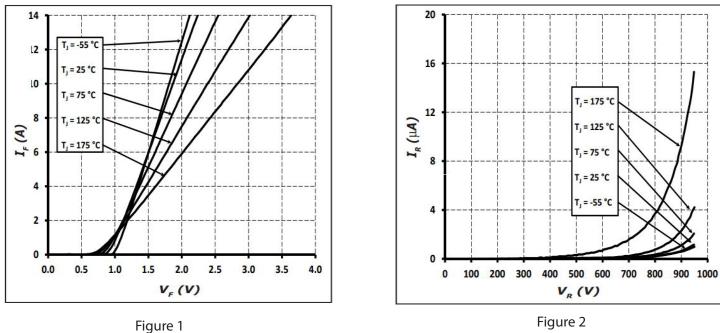
Parameter	Symbol	Value	Unit	Notes
Thermal Resistance, Junction to Case (Typical)	R _{0, JC (TYP)}	3.3	°C/W	
Junction Temperature	T _j	-55 to +175		
Case & Storage Temperature	T _c	-55 to +175	°C	
TO 220 Mounting Torque	_	1	Nm	M3 Screw
TO-220 Mounting Torque		8.8	lbf-in	6-32 Screw

Electrostatic Discharge (ESD) Classifications

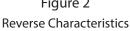
Parameter	Symbol	Notes
Human Body Model	HBM	Class 3B (≥ 8000 V)
Charge Device Model	CDM	Class C3 (≥ 1000 V)

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Typical Performance



Forward Characteristics



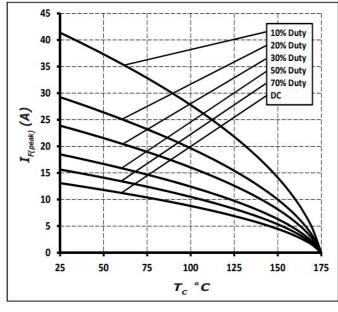
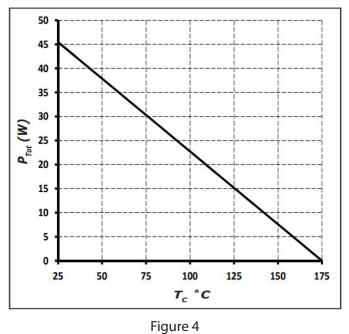


Figure 3 Current Derating



Power Derating

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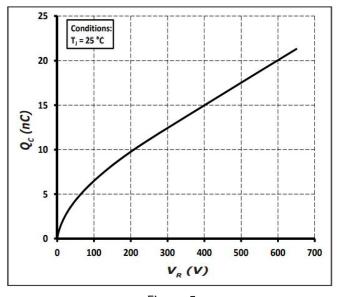


Figure 5 Total Capacitance vs. Reverse Voltage

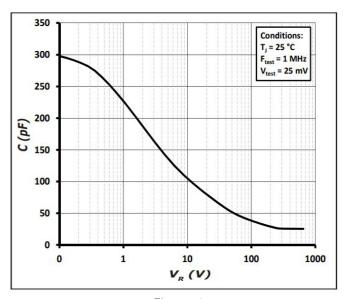


Figure 6 Capacitace vs. Reverse Voltage

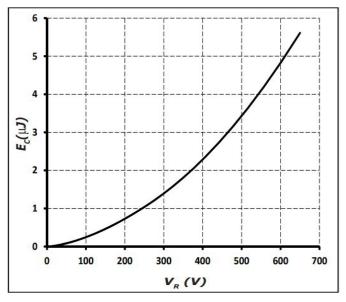


Figure 7 Capacitance Stored Energy

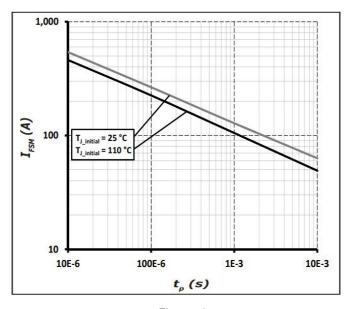


Figure 8 Non-Repetitive Peak Forward Surge Current versus Pulse Duration (sinusoidal waveform)

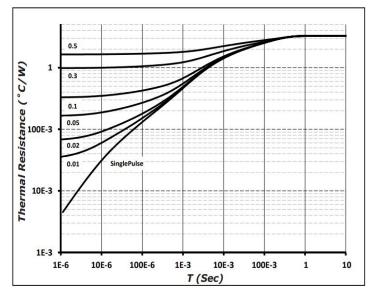
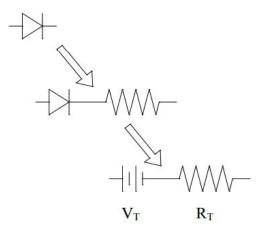


Figure 9 Transient Thermal Impedance

Diode Model



$$\begin{split} Vf_{T} &= V_{T} + \text{ If } * R_{T} \\ V_{T} &= 0.96 + (T_{J} * -1.1 * 10^{-3}) \\ R_{T} &= 0.07 + (T_{J} * 7.4 * 10^{-4}) \end{split}$$

Note: T_j = Diode Junction Temperature In Degrees Celsius, valid from 25°C to 175°C

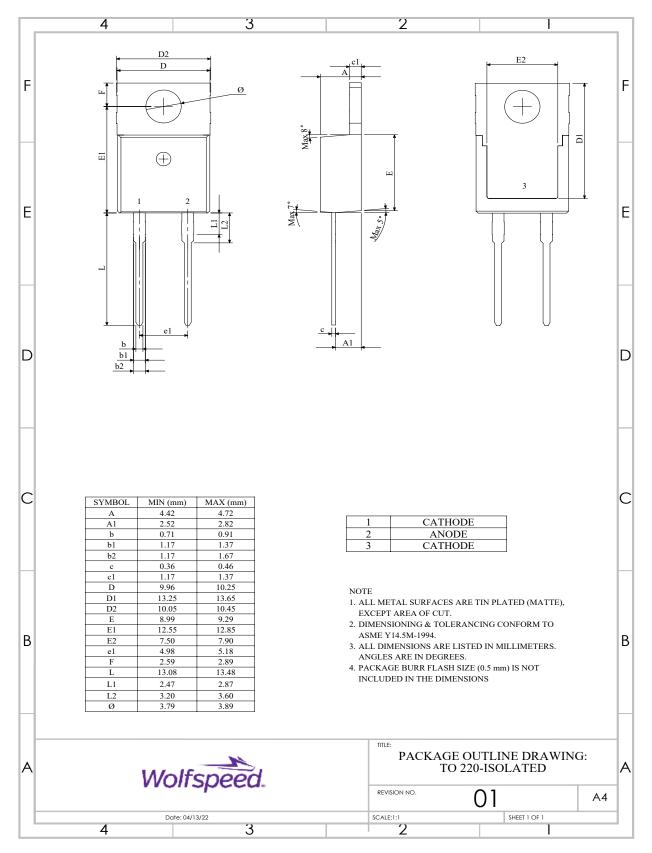
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Package Dimensions & Pin-Out

Package: TO-220-2



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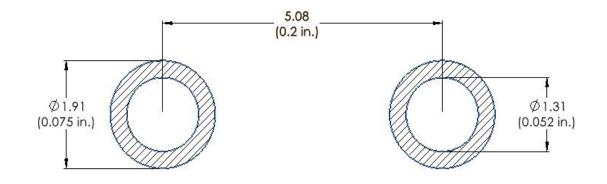
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Recommended Solder Pad Layout

Primary dimensions shown in mm.



Product Ordering Information

Order Number	Packing Type
C3D06065I	Tube

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Revision History

Document Version	Date of Release	Description of Changes
В	January-2016	Initial Release
4	May-2023	Update Package Drawing Update Landing Pad

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